

1. Material Substrate GaAs (N Type)
Epitaxial Layer AlGaAs (P/N Type)

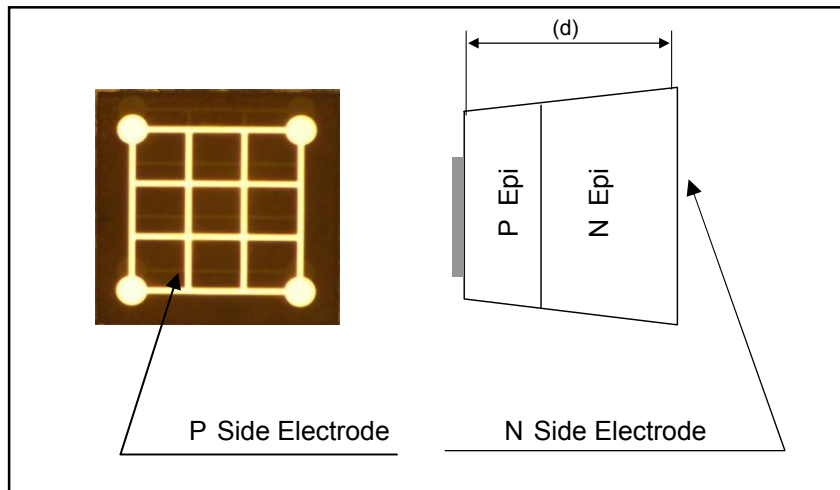
2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			2.1	V	IF=350mA
Reverse Current	V_R	4			V	IR=10uA
Power	P_O	17			mW	IF=350mA
Wavelength	λ_P		770		nm	IF=50mA
	$\Delta\lambda$		30		nm	IF=50mA

※ Note : LED chip is mounted on TO-18 gold header without resin coating

4. Mechanical Data (a) Emission Area ----- 39.0mil x 39.0mil
 (b) Bottom Area ----- 40.0mil x 40.0mil
 (c) Bonding Pad ----- 120um
 (d) Chip Thickness ----- 7.8mil



AUK Corp.

Eoyang factory, 513-5 Eoyang-dong, Iksan, 570-210, Korea
 Tel. +82 63 839 1111 Fax. +82 63 835 8259
www.auk.co.kr

